

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|---|------------------|
| - | 2 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (porous same grain\$1 same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/23 13:13 |
| - | 154 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 13:34 |
| - | 0 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same monolayer same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 10:42 |
| - | 0 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (monomolecular adj layer) same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 10:43 |
| - | 5 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (thin adj layer) same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 10:50 |
| - | 0 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (membrane) same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 10:50 |
| - | 154 | semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 13:34 |
| - | 28 | (semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and filter | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 13:41 |
| - | 0 | (semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer) and HF | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 13:42 |
| - | 5 | (semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 15:45 |
| - | 0 | semiconductor and (micromachined with encapsulation) and (permeable with polysilicon) and HF | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 15:46 |
| - | 0 | semiconductor and (micromachined with encapsulation) and (polysilicon) and HF | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 15:46 |
| - | 183 | semiconductor and (micromachined) and (polysilicon) and HF | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 15:47 |
| - | 0 | (semiconductor and (micromachined) and (polysilicon) and HF) and SiO and SiN | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/22 15:47 |

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|---|----|--|---|------------------|
| - | 24 | (semiconductor and (micromachined) and (polysilicon) and HF) and SiN | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:47 |
| - | 22 | ((semiconductor and (micromachined) and (polysilicon) and HF) and SiN) and oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:56 |
| - | 19 | Leboutitz.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:56 |
| - | 8 | Leboutitz.in. and polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:57 |
| - | 8 | (Leboutitz.in. and polysilicon) and oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:57 |
| - | 8 | ((Leboutitz.in. and polysilicon) and oxide) and nitride | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/22 15:57 |
| - | 10 | "718010" | USPAT; US-PGPUB | 2003/01/23 13:14 |